


PRODUCT / PROCESS CHANGE NOTIFICATION

1. PCN basic data

1.1 Company		STMicroelectronics International N.V
1.2 PCN No.	POWER AND DISCRETE PRODUCTS/24/14744	
1.3 Title of PCN	Introduction of 8" Diode on STGFW40V60DF	
1.4 Product Category	IGBT	
1.5 Issue date	2024-05-03	

2. PCN Team

2.1 Contact supplier	
2.1.1 Name	ROBERTSON HEATHER
2.1.2 Phone	+1 8475853058
2.1.3 Email	heather.robertson@st.com
2.2 Change responsibility	
2.2.1 Product Manager	Angelo RAO
2.1.2 Marketing Manager	Natale Sandro D'ANGELO
2.1.3 Quality Manager	Vincenzo MILITANO

3. Change

3.1 Category	3.2 Type of change	3.3 Manufacturing Location
General	Wafer diameter modification	Tours

4. Description of change

	Old	New
4.1 Description	The current IGBT STGFW40V60DF is assembled with a 6" co-packaged Diode	The IGBT STGFW40V60DF will be assembled with the same co-packaged Diode diffused on a 8" wafer
4.2 Anticipated Impact on form,fit, function, quality, reliability or processability?	processability	

5. Reason / motivation for change

5.1 Motivation	Service improvement
5.2 Customer Benefit	SERVICE CONTINUITY

6. Marking of parts / traceability of change

6.1 Description	By internal traceability and dedicated FG code
-----------------	--

7. Timing / schedule

7.1 Date of qualification results	2024-05-03
7.2 Intended start of delivery	2024-08-03
7.3 Qualification sample available?	Upon Request

8. Qualification / Validation

8.1 Description	14744 Binder1.pdf		
8.2 Qualification report and qualification results	Available (see attachment)	Issue Date	2024-05-03

9. Attachments (additional documentations)

14744 Public product.pdf
14744 14744.pdf
14744 Binder1.pdf

10. Affected parts		
10. 1 Current		10.2 New (if applicable)
10.1.1 Customer Part No	10.1.2 Supplier Part No	10.1.2 Supplier Part No
	STGFW40V60DF	

IMPORTANT NOTICE – PLEASE READ CAREFULLY

Subject to any contractual arrangement in force with you or to any industry standard implemented by us, STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2022 STMicroelectronics – All rights reserved



Product/process change notification:

Introduction of 8" Diode on STGFW40V60DF

POWER AND DISCRETE PRODUCTS/24/14744

Description of the change

Analog, Power & Discrete, MEMS & Sensors (APMS)
Power Transistor Sub-Group
IGBT & IPM Division
IGBT Business Unit
Industrial

Dear Customer,

Following the continuous improvement of our service, we are going to introduce the 8" version of the Diode on the IGBT STGFW40V60DF, currently manufactured with the 6" version.
No changes are expected in the product performances.

Involved Product	Package	Test Vehicle	Samples Availability
IGBT	TO3PF	STGFW40V60DF	Available

Yours faithfully

April 29, 2024

Product/process change notification:
Introduction of 8" Diode on STGFW40V60DF

POWER AND
DISCRETE
PRODUCTS/24/14744

Reason

Service improvement

Date of implementation

August, 2024

Impact of the change

Form	
Fit	
Function	
Reliability	
Processibility	X

Qualification of the change

See attached Qualification reports.

IMPORTANT NOTICE—PLEASE READ CAREFULLY

Subject to any contractual arrangement in force with you or to any industry standard implemented by us, STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgment.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2022 STMicroelectronics—All rights reserved

IGBT Trench Gate FS Emitter Implant Technology

Diode 8" wafer fab activation in Tours (France)

Industrial Domain

Reliability Evaluation Report

Note: this report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the electronic device conformance to its specific mission profile for Industrial Application. This report and its contents shall not be disclosed to a third party without previous written agreement from STMicroelectronics or under the approval of the author (see below).

Revision history

Rev.	Changes description	Author	Date
1.0	First release	M. Panzarella	August 30 th , 2023

Approved by

Function	Location	Name	Date
Division Reliability Manager	ST Catania (Italy)	V.Giuffrida	August 30 th , 2023

Table of Contents

1.	Reliability Evaluation Overview.....	3
1.1.	Objective	3
1.2.	Reliability Strategy and Test Plan	3
1.2.1.	Reliability strategy.....	3
1.2.2.	Test Plan	4
	Test Plan Table.....	4
1.3.	Conclusion.....	4
2.	Product Characteristics.....	5
2.1.	Generalities	5
2.1.1.	Bonding diagram	5
2.2.	Traceability.....	6
2.2.1.	Wafer Fab information.....	6
2.2.2.	Assembly information	6
2.2.3.	Reliability Testing information	7
3.	Tests Results Summary.....	8
3.1.	Lot Information	8
3.2.	Test results summary (table).....	8

1. Reliability Evaluation Overview

1.1. Objective

Aim of this report is to present the results of the reliability evaluations performed on selected test vehicle to release in mass production the IGBT products with Diode manufactured in 8" wafer fab in ST Tours (France), intended for Industrial application domain, designed in Rectifier 600–650V Technology.

The qualification activity was performed on 4 different packages:

Commercial product	IGBT Silicon line/Die size	Diode silicon line/Die size	Package	Assembly plant
STGW80H65DFB-4	EWFR01 / 41 mm ²	FIH3 / 12.5 mm ²	TO247 4L	TFME subcon (China)
STGW80H65DFB		FHH6 / 23 mm ²	TO247	ST Shenzhen (China)
STGWA80H65DFB			TO247-LL	TFME subcon (China)
STGWT80H65DFB			TO3P-3L	SPSemi subcon (Korea)

1.2. Reliability Strategy and Test Plan

1.2.1. Reliability strategy

Reliability trials performed as part of this reliability evaluation are in agreement with **ST 0061692** specification and are listed in below Test Plan. For details on test conditions, generic data used and specifications references, refer to test results summary in section 3.

1.2.2. Test Plan

Test Plan Table

#	TEST NAME	DESCRIPTION / COMMENTS	TEST FLAG
1	TEST	Pre- and Post- Stress Electrical Test	Yes
2	PC	Preconditioning	Not Applicable
3	EV	Eternal Visual	Yes
4	HTRB	High Temperature Reverse Bias	Yes
5	HTGB	High Temperature Gate Bias	No
6	TC	Temperature Cycling	Yes
7	AC	Autoclave	Yes
8	THB	Temperature Humidity Bias	Yes
9	IOL	Intermittent Operational Life	Yes
10	ESD	ESD Characterization	No

1.3. Conclusion

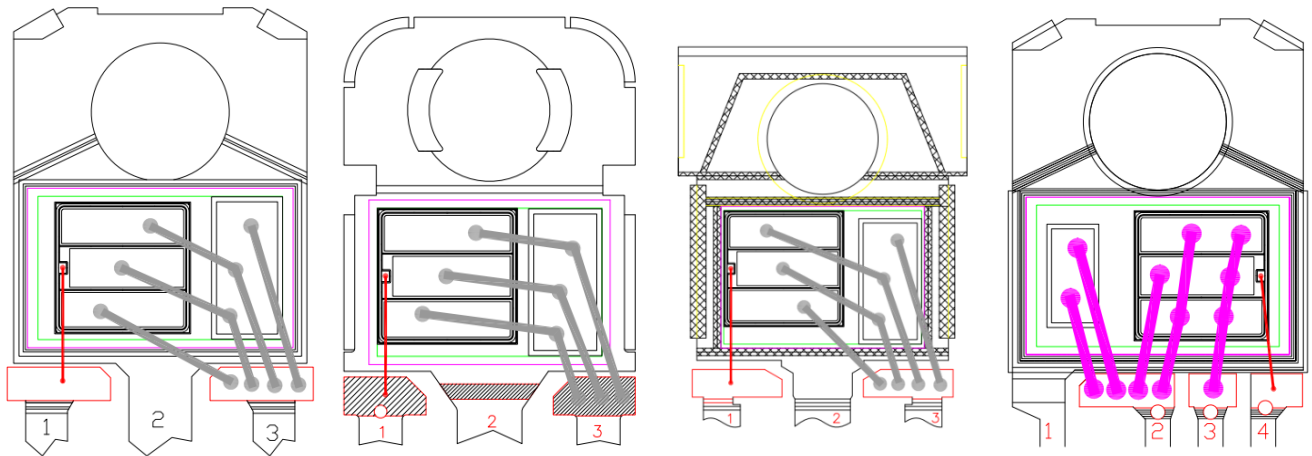
All reliability tests have been completed with positive results on all samples/Lots. Neither functional nor parametric rejects were detected at final electrical testing.

Based on the overall results obtained, the IGBT products with Diode manufactured in 8" wafer fab in ST Tours (France), intended for Industrial application domain, designed in Rectifier 600-650V Technology, have positively passed reliability evaluation performed in agreement with ST internal specification #0061692

2. Product Characteristics

2.1. Generalities

2.1.1. Bonding



2.2. Traceability

2.2.1. Wafer Fab information

Wafer fab name / location	ST CT8 Catania (Italy)
Wafer diameter (inches)	8"
Silicon process technology	IGBT Trench gate field-stop Emitter Implant
Die finishing front side	SiN
Die finishing back side	Al/Ti/NiV/Ag
Die size (micron)	6500 x 6300 um
Metal levels/ materials/ thicknesses	Ti/TiN, 0115um/ W, 0.8 um / AlCu 4.5um

2.2.2. Assembly information

STGW80H65DFB-4	
Assembly plant name / location	TFME Tongfu (China) subcon
Package description	TO247-4L
Lead frame/Substrate	TO247-4L LL Full Ni, raw Cu on frame pad
Die attach material	Preform (Pb free) Sn/Ag25/Sb10
Wire bonding material/diameter	Al 20 mils Source - Al 5 mils Gate
Molding compound material	Sumitomo EME500HA
Package Moisture Sensitivity Level (JEDEC J-STD020D)	Not Applicable

STGW80H65DFB	
Assembly plant name / location	ST Shenzhen (China)
Package description	TO247
Lead frame/Substrate	FRAME TO247 3L Mon Ve6 OpA/Q SeNi/NiP
Die attach material	PREFORM Pb/Ag/Sn 95.5/2.5/2 D.76mm SSD
Wire bonding material/diameter	Al 15 mils Source - Al 5 mils Gate
Molding compound material	RESIN LOCTITE HYSOL GR30
Package Moisture Sensitivity Level (JEDEC J-STD020D)	Not Applicable

STGWA80H65DFB	
Assembly plant name / location	TFME Tongfu (China) subcon
Package description	TO247-LL
Lead frame/Substrate	TO247-3A(IP CU)LL Full Ni raw Cu on frame pad
Die attach material	SnAg25Sb10
Wire bonding material/diameter	Al 15 mils Source - Al 5 mils Gate
Molding compound material	Sumitomo EME-E500HA green
Package Moisture Sensitivity Level (JEDEC J-STD020D)	Not Applicable

STGWT80H65DFB	
Assembly plant name / location	SPSemi (Korea) subcon
Package description	TO3P-3L
Lead frame/Substrate	TY-TO3P L/F SPD-7005/03Type1Ni PinPostPLated
Die attach material	SOFT SOLDER Pb/Ag/Sn 95.5/2.5/2
Wire bonding material/diameter	Al 15 mils Source - Al 5 mils Gate
Molding compound material	KCC KTMC-1050GR Green
Package Moisture Sensitivity Level (JEDEC J-STD020D)	Not Applicable

2.2.3. Reliability Testing information

Reliability laboratory location	STM Catania (Italy)
---------------------------------	---------------------

3. Tests Results Summary

3.1. Lot Information

Lot #	Commercial product	Diffusion Lot	Assembly Lot	Note
Lot1	STGWA80H65DFB (EWFR silicon line)	C248HT0V01	GF308242	
Lot2	STGW80H65DFB (EWFR silicon line)	C925E66	GK3067W8	
Lot3	STGW80H65DFB (EWFR silicon line)	C248HT0	GF310001	
Lot4	STGWT80H65DFB (EWFR silicon line)	C3013L6	HB320012	

3.2. Test results summary (table)

Test method revision reference is the one active at the date of reliability trial execution.

Test	#	Reference	STM Test Conditions	Lots	S.S.	Total	Results FAIL/SS/Lots	Comments
TEST	1		User specification or supplier's standard specification	4	145	580	0/145/4	All qualification parts
PC	2	-	-	-	-	-	-	
EV	3	JESD22B-1011	All qualification parts submitted for testing	4	145	580	Passed	
HTRB	4	MIL-STD-750-1 M1038 Method A	(KGJR) Tj=175°C, Vces=960V, 1000h (EWFR/JWF7) Tj=175°C, Vces=520V, 1000h	4	45	180	0/45/4	
HTGB	5	JESD22 A-108	-	-	-	-	-	
TC	6	JESD22A-104	Ta=-55°C /+150°C, 1000cy	4	25	100	0/25/4	
AC	7	JESD22 A-102	Ta=121°C, Pa=2atm, RH=100%, 96 hours	4	25	100	0/25/4	
THB	8	JESD22A-101	Ta=85°C, RH=85% Vds=100V, 1000h	4	25	100	0/25/4	
IOL	9	MIL-STD-750 Method 1037	15Kcy @ Ta=25°C with parts powered to insure $\Delta T_j \geq 100^\circ\text{C}$ (not to exceed absolute maximum ratings).	4	25	100	0/25/4	
ESD	10	JEDEC JS-001 & JS-002	-	-	-	-	-	

TERMS OF USE

BY ACCEPTING THIS REPORT, YOU AGREE TO THE FOLLOWING TERMS OF USE:

This Reliability Evaluation Report (the "Report") and all information contained herein is the property of STMicroelectronics ("ST") and is provided solely for the purpose of obtaining general information relating to an ST product. Accordingly, you hereby agree to make use of this Report solely for the purpose of obtaining general information relating to the ST product. You further acknowledge and agree that this Report may not be used in or in connection with any legal or administrative proceeding in any court, arbitration, agency, commission or other tribunal or in connection with any action, cause of action, litigation, claim, allegation, demand or dispute of any kind. You further acknowledge and agree that this Report shall not be construed as an admission, acknowledgement or evidence of any kind, including, without limitation, as to the liability, fault or responsibility whatsoever of ST or any of its affiliates, or as to the accuracy or validity of the information contained herein, or concerning any alleged product issue, failure, or defect. ST does not promise that this Report is accurate or error free and specifically disclaims all warranties, express or implied, as to the accuracy of the information contained herein. Accordingly, you agree that in no event will ST or its affiliates be liable to you for any direct, indirect, consequential, exemplary, incidental, punitive, or other damages, including lost profits, arising from or relating to your reliance upon or use of this Report. You further acknowledge and agree that the use of this Report in violation of these Terms of Use would cause immediate and irreparable harm to ST which could not adequately be remedied by damages. You therefore agree that injunctive relief is an appropriate remedy to enforce these Terms of Use.

Disclosure of this document to any non-authorized party must be previously authorized by ST only under the provision of a proper confidentiality contractual arrangement executed between ST and you and must be treated as strictly confidential.

At all times you will comply with the following security rules:

- Do not copy or reproduce all or part of this document
- Keep this document locked away
- Further copies can be provided on a "need to know basis", Please contact your local ST Sales Office or document writer

Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement, including, without limitation, the warranty provisions thereunder.

In that respect please note that ST products are not designed for use in some specific applications or environments described in above mentioned terms and conditions.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

Information furnished is believed to be accurate and reliable. However, ST assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license, express or implied, to any intellectual property right is granted by ST herein.

ST and ST logo are trademarks of ST. All other product or service names are the property of their respective owners. Information in this document supersedes and replaces information previously supplied in any prior version of this document.

Reliability Evaluation Report

STGFW40V60DF

Samsung wafer foundry activation 2nd source

Note: this report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the electronic device conformance to its specific mission profile for Industrial Application. This report and its contents shall not be disclosed to a third party without previous written agreement from STMicroelectronics or under the approval of the author (see below).

Revision history

Rev.	Changes description	Author	Date
1.0	First release	M. Panzarella	April 23 rd , 2024

Approved by

Function	Location	Name	Date
Division Reliability Manager	ST Catania (Italy)	M.De Tomasi	April 23 rd , 2024

Table of Contents

1.	Reliability Evaluation Overview.....	3
1.1.	Objective	3
1.2.	Reliability Strategy and Test Plan	3
1.2.1.	Reliability strategy.....	3
1.2.2.	Test Plan	4
	Test Plan Table.....	4
1.3.	Conclusion.....	4
2.	Product Characteristics.....	5
2.1.	Traceability.....	5
2.1.1.	Wafer Fab information.....	5
2.1.2.	Assembly information	5
2.1.3.	Reliability Testing information	5
3.	Tests Results Summary.....	6
3.1.	Lot Information	6
3.2.	Test results summary (table)	6

1. Reliability Evaluation Overview

1.1. Objective

Aim of this report is to present the results of the reliability evaluation to release in mass production the product **STGFW40V60DF** (EVF6+P500 as ST silicon line), designed in IGBT Trench Gate FS Emitter Implant Technology intended for standard application domain, diffused in Samsung wafer Foundry as 2nd source and assembled in SP Semi subcon (Korea) in package TO3PF.

1.2. Reliability Strategy and Test Plan

1.2.1. Reliability strategy

The products designed in IGBT Trench Gate Field Stop Emitter Implant Technology, were already released in mass production for silicon diffused in Samsung wafer Foundry in combination with different packages by means a full qualification path as reported in the evaluation document # RRPTD21095 dated December 14th, 2021.

To extend these results to the product **STGFW40V60DF** (EVF6+P500 as ST silicon line) classified as DERIVATIVE, a delta evaluation was performed on 1 lot to cover the package TO3PF assembled in SP Semi subcon (Korea).

The IGBT products with Diode manufactured in 8" wafer fab in ST Tours (France), intended for Industrial application domain, designed in Rectifier 600–650V Technology, were already released in mass production by means selected test vehicles (refer to the report # RERPTD23066 dated August 30th, 2023) extending these results to the product **STGFW40V60DF** (EVF6+FIH3 as ST silicon line) is considered DERIVATIVE.

For details on test conditions, generic data used and specifications references, refer to test results summary in section 3.

1.2.2. Test Plan

Test Plan Table on products

#	TEST NAME	DESCRIPTION / COMMENTS	TEST FLAG
1	TEST	Pre- and Post- Stress Electrical Test	Yes
2	PC	Preconditioning	Not Applicable
3	EV	Eternal Visual	Yes
4	HTRB	High Temperature Reverse Bias	Similarity (generic data)
5	HTGB	High Temperature Gate Bias	Similarity (generic data)
6	TC	Temperature Cycling	Yes
7	AC	Autoclave	Yes
8	THB	Temperature Humidity Bias	Yes
9	IOL	Intermittent Operational Life	Yes
10	ESD	ESD Characterization	Yes

1.3. Conclusion

All reliability tests have been completed with positive results. Neither functional nor parametric rejects were detected at final electrical testing.

Based on the overall results obtained the product **STGFW40V60DF** (EVF6+P500 as ST silicon line), designed in IGBT Trench Gate FS Emitter Implant Technology intended for standard application domain, diffused in Samsung wafer foundry as 2nd source, has positively passed reliability evaluation performed in agreement with ST 0061692 specification.

The positive results are extended to all products classified as Derivative.

2. Product Characteristics

2.1. Traceability

2.1.1. Wafer Fab information

Wafer fab name / location	Samsung wafer foundry
Wafer diameter (inches)	8"
Silicon process technology	IGBT Trench Gate FS Emitter Implant
Die finishing front side	SiN
Die finishing back side	Al/Ti/NiV/Ag
Die size (micron)	5440 x 4000 um2
Metal levels/ materials/ thicknesses	1 level Ti/TiN 0.115um, W 0.8um, AlCu 4.5um

2.1.2. Assembly information

Assembly plant name / location	SP Semi (Korea) subcon
Package description	TO3P-PF
Lead frame/Substrate	TO3P-FP DWG#SPD-7009 RAW Cu SPOT Ni
Die attach material	SOFT SOLDER (95.5%PB/ 2%SN/ 2.5AG)
Wire bonding material/diameter	Al 15 mils Source – Al 5 mils Gate
Molding compound material	MP4000H6-S (NITTO)
Package Moisture Sensitivity Level	Not applicable

2.1.3. Reliability Testing information

Reliability laboratory location	STM Catania (Italy)
---------------------------------	---------------------

3. Tests Results Summary

3.1. Lot Information

Lot #	Commercial Product	Package	Diffusion Lot#	Assembly Lot#	Note
Lot1	STGFW40V60DF (EVF6 + P500 as ST Silicon line)	TO3PF	68Z89U	HB213004	

3.2. Test results summary (table)

Test method revision reference is the one active at the date of reliability trial execution.

Test	#	Reference	STM Test Conditions	Lots	S.S.	Total	Results FAIL/SS/Lots	Comments
TEST	1		User specification or supplier's standard specification	1	326	326	0/326/1	All qualification parts
PC	2	JESD020E	–	–	–	–	–	
EV	3	JESD22B-1011	All qualification parts submitted for testing	1	326	326	Passed	
HTRB	4	MIL-STD-750-1 M1038 Method A	Tj=175°C, Vce=480V, 1000h	–	–	–	Similarity (generic data)	S.S. 45x3Lots
HTGB	5	JESD22 A-108	Tj=175°C, Vge= 20V, 1000h	–	–	–	Similarity (generic data)	S.S. 45x3Lots
HTGB	6	JESD22 A-108	Tj=175°C, Vge= -20V, 1000h	–	–	–	Similarity (generic data)	S.S. 45x3Lots
TC	7	JESD22A-104	Ta=-55°C /+150°C, 1000cy	1	77	308	0/77/4	
AC	8	JESD22 A-102	Ta=121°C, Pa=2atm, RH=100%, 96h	1	77	308	0/77/4	
THB	9	JESD22A-101	Ta=85°C, RH=85% Vce=100V, 1000h	1	77	308	0/77/4	
IOL	10	MIL-STD-750 Method 1037	15Kcy @ Ta=25°C with parts powered to insure $\Delta Tj \geq 100^\circ\text{C}$ (not to exceed absolute maximum ratings).	1	77	308	0/77/4	
ESD	11	JESD22-A114 JESD22-A115	HBM / CDM	1	18	18	HBM Class 3B CDM Class C3	

TERMS OF USE

BY ACCEPTING THIS REPORT, YOU AGREE TO THE FOLLOWING TERMS OF USE:

This Reliability Evaluation Report (the "Report") and all information contained herein is the property of STMicroelectronics ("ST") and is provided solely for the purpose of obtaining general information relating to an ST product. Accordingly, you hereby agree to make use of this Report solely for the purpose of obtaining general information relating to the ST product. You further acknowledge and agree that this Report may not be used in or in connection with any legal or administrative proceeding in any court, arbitration, agency, commission or other tribunal or in connection with any action, cause of action, litigation, claim, allegation, demand or dispute of any kind. You further acknowledge and agree that this Report shall not be construed as an admission, acknowledgement or evidence of any kind, including, without limitation, as to the liability, fault or responsibility whatsoever of ST or any of its affiliates, or as to the accuracy or validity of the information contained herein, or concerning any alleged product issue, failure, or defect. ST does not promise that this Report is accurate or error free and specifically disclaims all warranties, express or implied, as to the accuracy of the information contained herein. Accordingly, you agree that in no event will ST or its affiliates be liable to you for any direct, indirect, consequential, exemplary, incidental, punitive, or other damages, including lost profits, arising from or relating to your reliance upon or use of this Report. You further acknowledge and agree that the use of this Report in violation of these Terms of Use would cause immediate and irreparable harm to ST which could not adequately be remedied by damages. You therefore agree that injunctive relief is an appropriate remedy to enforce these Terms of Use.

Disclosure of this document to any non-authorized party must be previously authorized by ST only under the provision of a proper confidentiality contractual arrangement executed between ST and you and must be treated as strictly confidential.

At all times you will comply with the following security rules:

- Do not copy or reproduce all or part of this document
- Keep this document locked away
- Further copies can be provided on a "need to know basis", Please contact your local ST Sales Office or document writer

Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement, including, without limitation, the warranty provisions thereunder.

In that respect please note that ST products are not designed for use in some specific applications or environments described in above mentioned terms and conditions.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

Information furnished is believed to be accurate and reliable. However, ST assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license, express or implied, to any intellectual property right is granted by ST herein.

ST and ST logo are trademarks of ST. All other product or service names are the property of their respective owners. Information in this document supersedes and replaces information previously supplied in any prior version of this document.

©2020 STMicroelectronics – All rights reserved



Public Products List

Public Products are off the shelf products. They are not dedicated to specific customers, they are available through ST Sales team, or Distributors, and visible on ST.com

PCN Title : Introduction of 8" Diode on STGFW40V60DF
PCN Reference : POWER AND DISCRETE PRODUCTS/24/14744

Subject : Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

STGFW40V60DF		
--------------	--	--

IMPORTANT NOTICE – PLEASE READ CAREFULLY

Subject to any contractual arrangement in force with you or to any industry standard implemented by us, STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2022 STMicroelectronics – All rights reserved